

<b>SANYO</b>	No.1048B	<b>2SA1252/2SC3134</b>
		PNP/NPN Epitaxial Planar Silicon Transistors For AF Applications

**Features**

- . High  $V_{EBO}$ .
- . Wide ASO and high durability against breakdown.

( ) : 2SA1252

**Absolute Maximum Ratings at  $T_a=25^\circ\text{C}$**

Collector to Base Voltage	$V_{CBO}$	(-) 60	V
Collector to Emitter Voltage	$V_{CEO}$	(-) 50	V
Emitter to Base Voltage	$V_{EBO}$	(-) 15	V
Collector Current	$I_C$	(-) 150	mA
Collector Current(Pulse)	$I_{CP}$	(-) 300	mA
Collector Dissipation	$P_C$	200	mW
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

**Electrical Characteristics at  $T_a=25^\circ\text{C}$**

			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=(-)40\text{V}, I_E=0$			(-)0.1	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=(-)10\text{V}, I_C=0$			(-)0.1	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE}=(-)6\text{V}, I_C=(-)1\text{mA}$	90*		560*	
Gain-Bandwidth Product	$f_T$	$V_{CE}=(-)6\text{V}, I_C=(-)1\text{mA}$		100		MHz
Output Capacitance	$c_{ob}$	$V_{CB}=(-)6\text{V}, f=1\text{MHz}$		(3.5)		pF
				2.2		
C to E Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)50\text{mA}, I_B=(-)5\text{mA}$			(-)0.5	V
C to B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu\text{A}, I_E=0$	(-)60			V
C to E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1\text{mA}, R_{BE}=\infty$	(-)50			V
E to B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu\text{A}, I_C=0$	(-)15			V

\*The 2SA1252/2SC3134 are classified as follows according to  $h_{FE}$  at 1mA:

90	4	180	135	5	270	200	6	400	300	7	600
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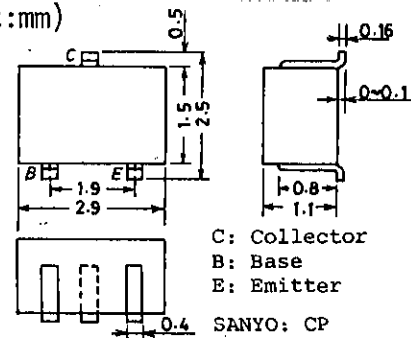
Marking 2SA1252 : D

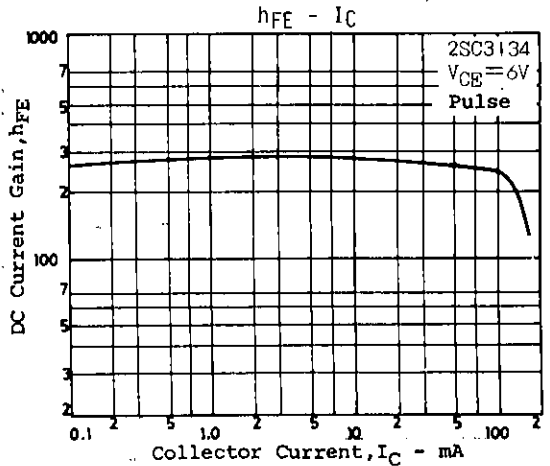
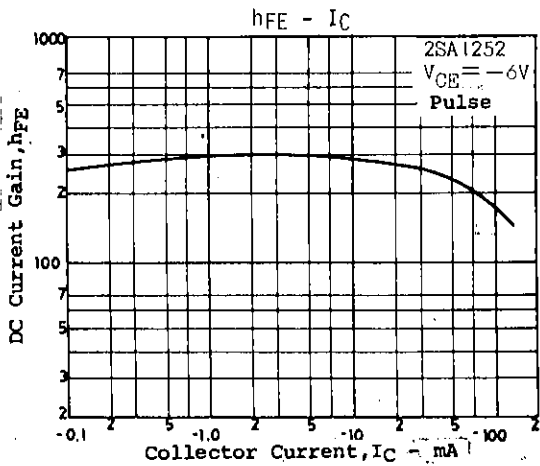
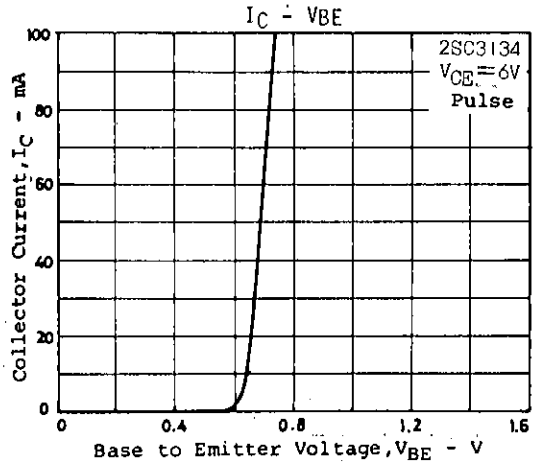
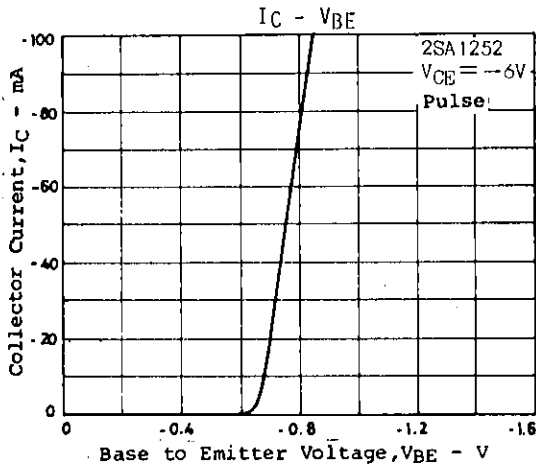
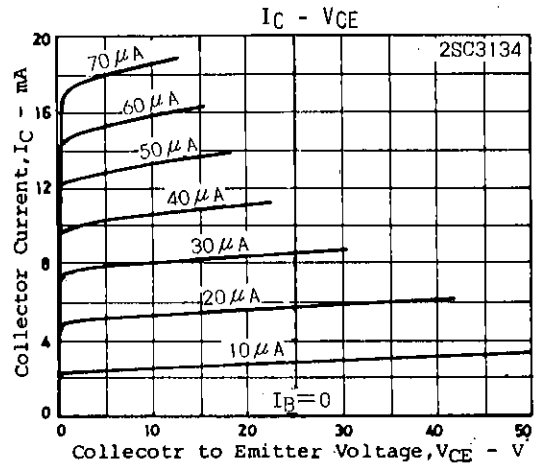
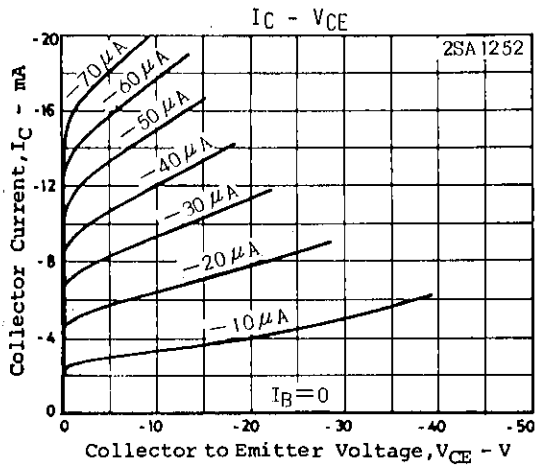
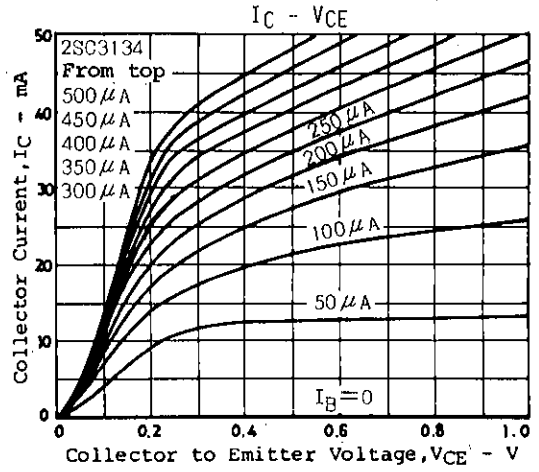
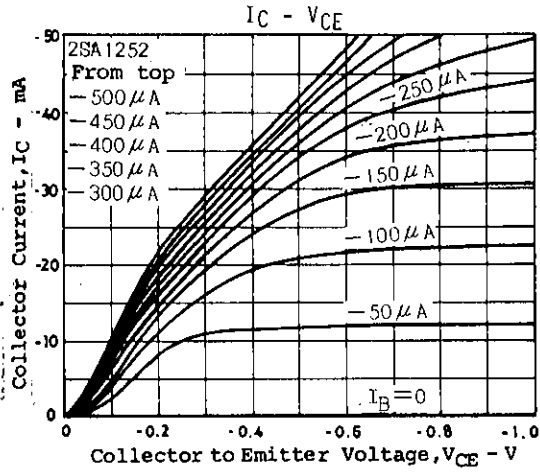
2SC3134 : H

$h_{FE}$  rank : 4,5,6,7

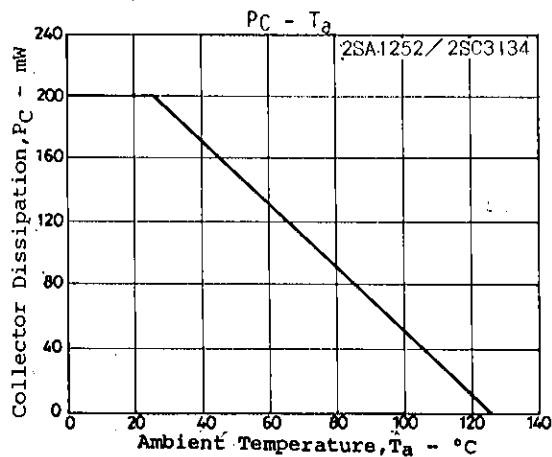
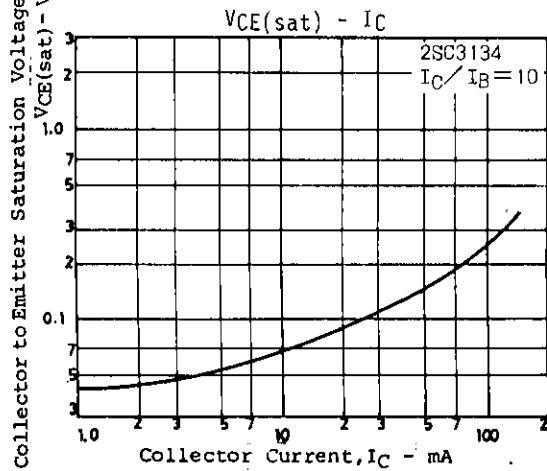
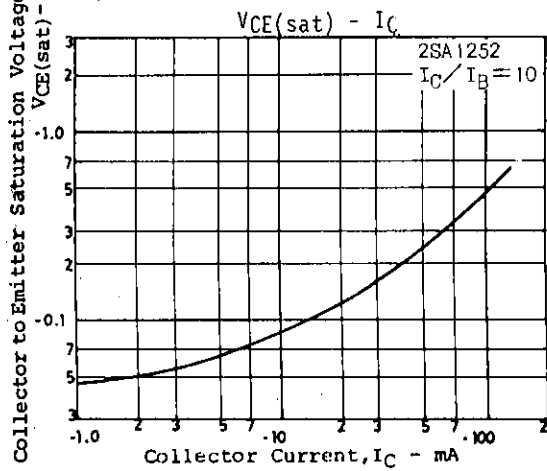
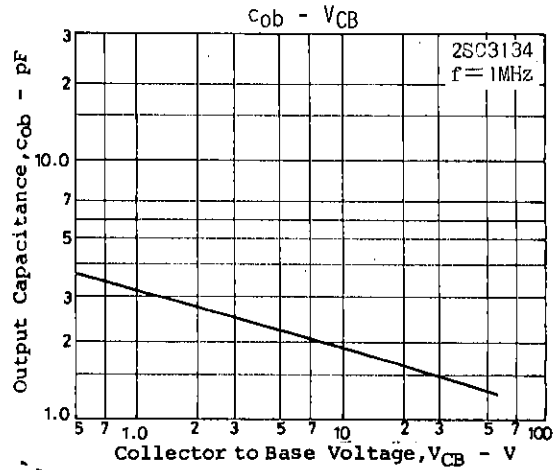
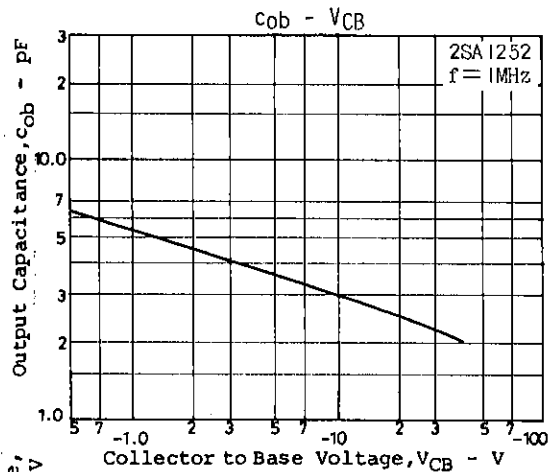
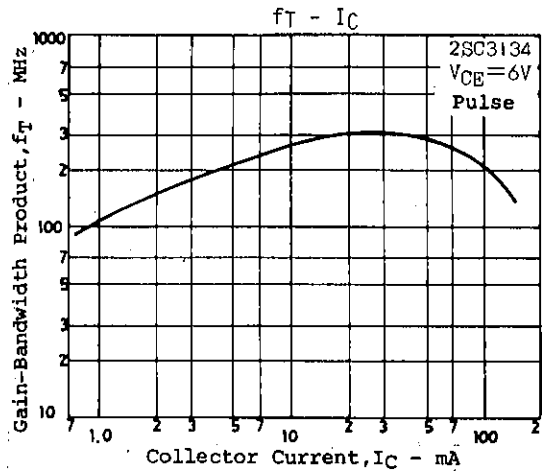
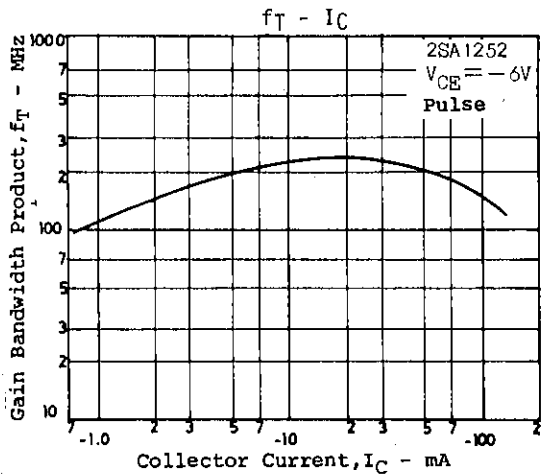
**Package Dimensions 2018A**

(unit:mm)





2SA1252/2SC3134



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